

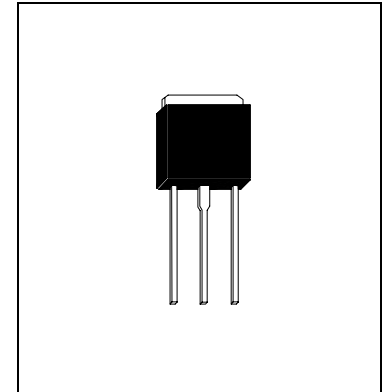


HI3669

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The HI3669 is designed for using in power amplifier applications, power switching application.



Absolute Maximum Ratings (Ta=25°C)

- Maximum Temperatures
 Tstg Storage Temperature -55 ~ +150 °C
 Tj Junction Temperature +150 °C
- Maximum Power Dissipation
 Total Power Dissipation (Ta=25°C) 1.25 W
- Maximum Voltages and Currents
 BVCBO Collector to Base Breakdown Voltage 80 V
 BVCEO Collector to Emitter Breakdown Voltage 80 V
 BVEBO Emitter to Base Emitter Breakdown Voltage 5 V
 IC Collector Current (DC)..... 2 A

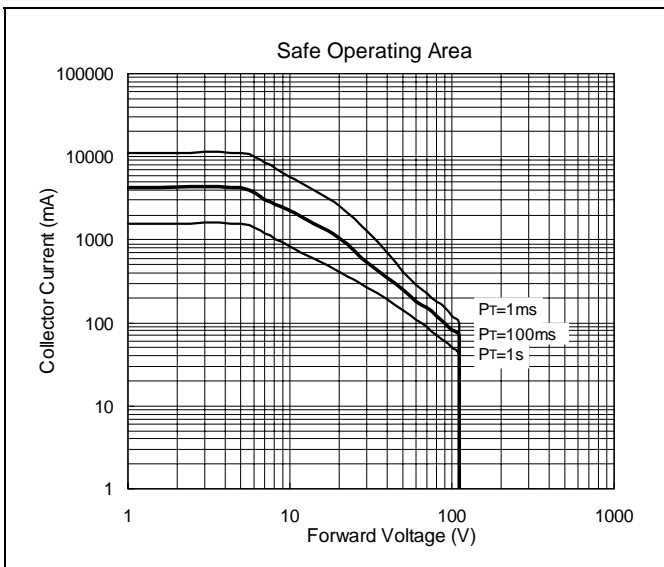
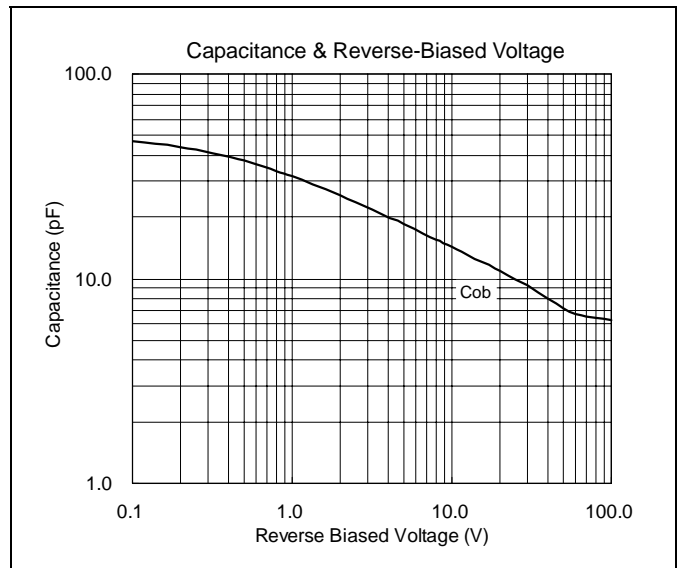
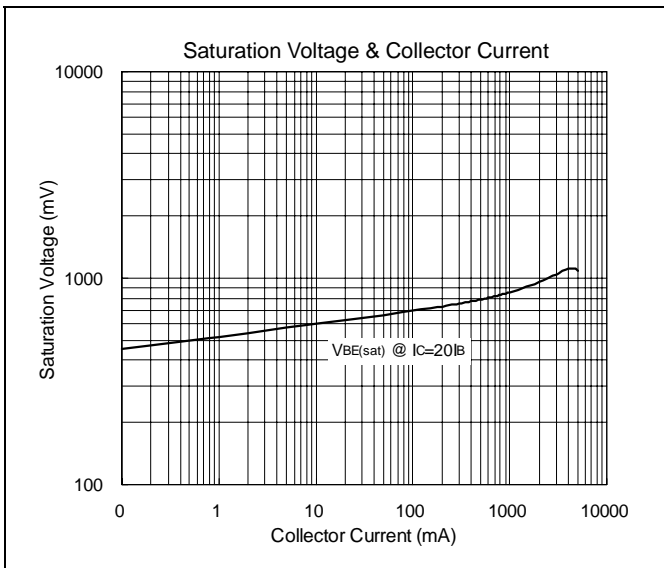
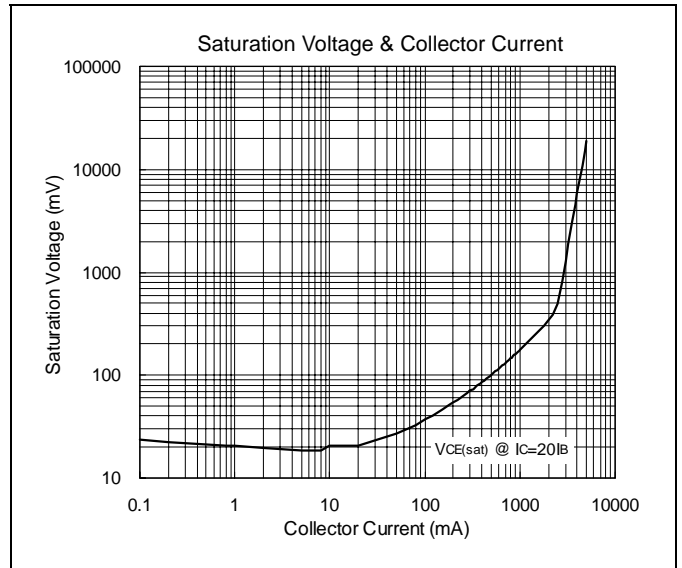
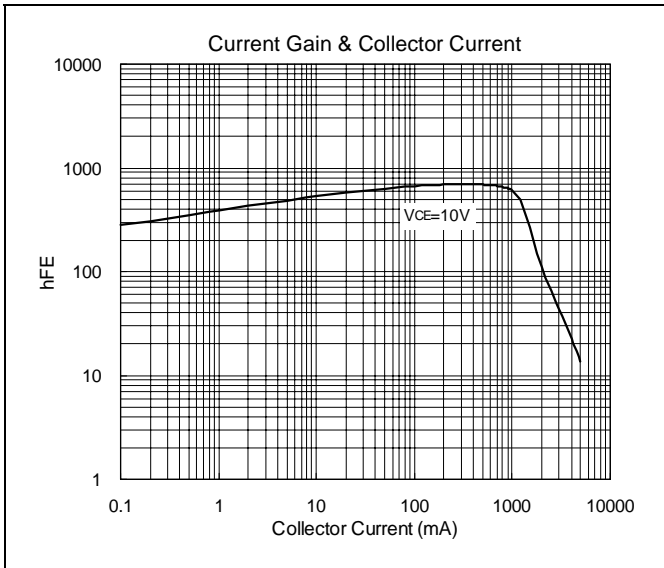
Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	80	-	-	V	IC=100uA
BVCEO	80	-	-	V	IC=10mA
BVEBO	5	-	-	V	IE=100uA
ICBO	-	-	1000	nA	VCB=80V
IEBO	-	-	1000	nA	VEB=5V
*VCE(sat)	-	0.15	0.5	V	IC=1A, IB=50mA
*VBE(sat)	-	0.9	1.2	V	IC=1A, IB=50mA
*hFE	300	-	-		VCE=2V, IC=500mA
fT	-	100	-	MHz	VCE=2V, IC=500mA
Cob	-	30	-	pF	VCB=10V, f=1MHz
Ton	-	0.2	-	uS	IB1=-IB2=50mA, Duty Cycle≤1%
Tstg	-	1.0	-	uS	
Tf	-	0.2	-	uS	

*Pulse Test : Pulse Width ≤380us, Duty Cycle≤2%

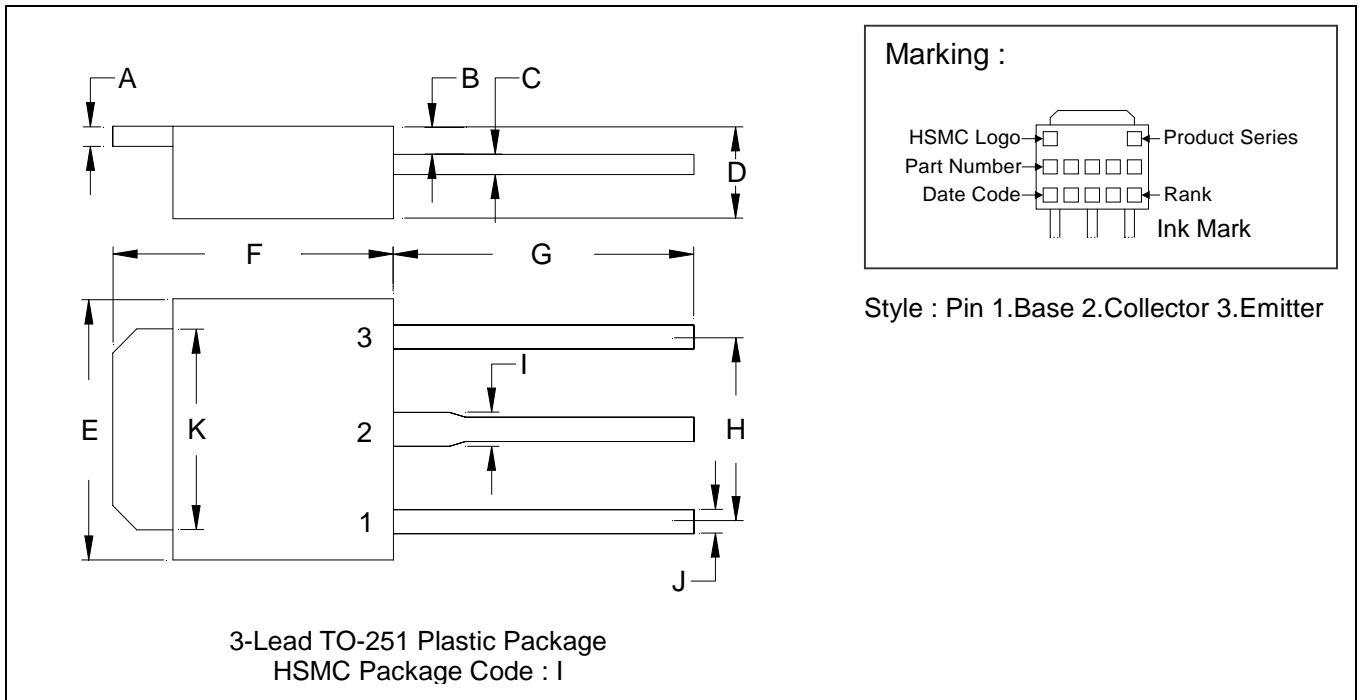


Characteristics Curve





TO-251 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.2559	-	6.50	-
B	0.0354	0.0591	0.90	1.50	H	-	*0.1811	-	*4.60
C	0.0177	0.0236	0.45	0.60	I	-	0.0354	-	0.90
D	0.0866	0.0945	2.20	2.40	J	-	0.0315	-	0.80
E	0.2520	0.2677	6.40	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2677	0.2835	6.80	7.20					

Notes : 1.Dimension and tolerance based on our Spec. dated May. 24,1995.
 2.Controlling dimension : millimeters.
 3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

Material :

- Lead : 42 Alloy ; solder plating
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0

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